

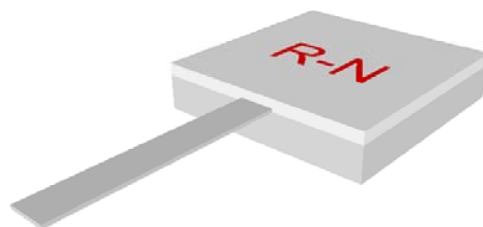
RPC250-250-4T50-5C

DC-8GHz HIGH POWER TERMINATION

The RPC250-250-4T50-5C offers excellent performance to 8 GHz. This high power chip termination handles 100W which makes it ideal for different applications in various commercial and military frequency bands. The RPC250-250-4T50-5C is also RoHS compliant.

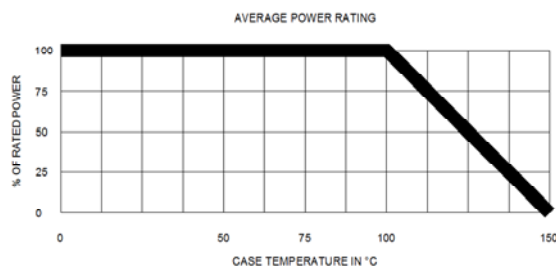
Features:

- Low VSWR
- DC-8 GHz
- BeO Substrate
- 100 Watts
- RoHS Compliant

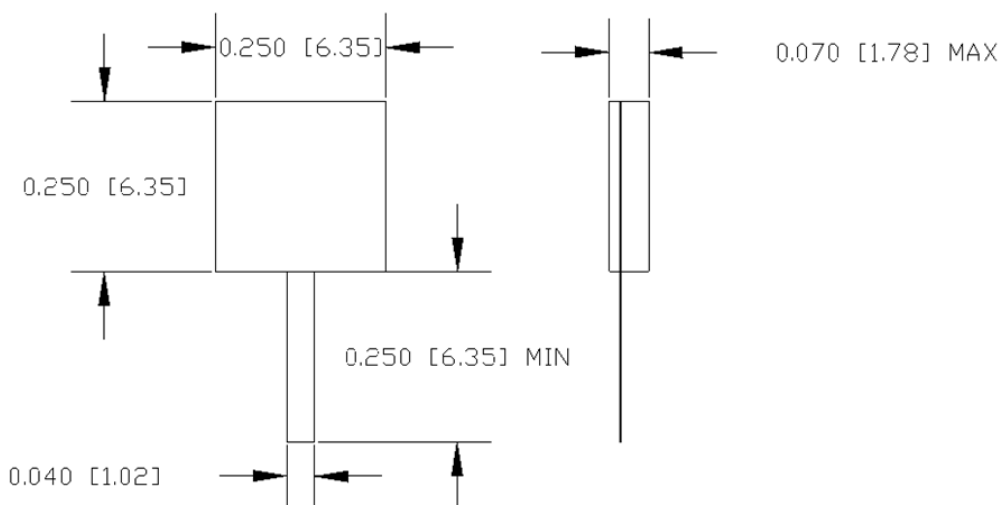


Specifications:

- Resistance: 50 Ohms, +/-5%
- Frequency: DC - 8 GHz
- Power: 100 Watts
- VSWR 1.2:1
- Operating Temperature: -55°C to 150°C



Mechanical Outline



Dimensions are in inches [mm]

P.O. BOX 18802, Clearwater, FL 33762
1-800-526-0704

RPC250-250-4T50-5C

DC-8GHZ HIGH POWER CHIP TERMINATION

Typical Performance

S11 FORWARD REFLECTION

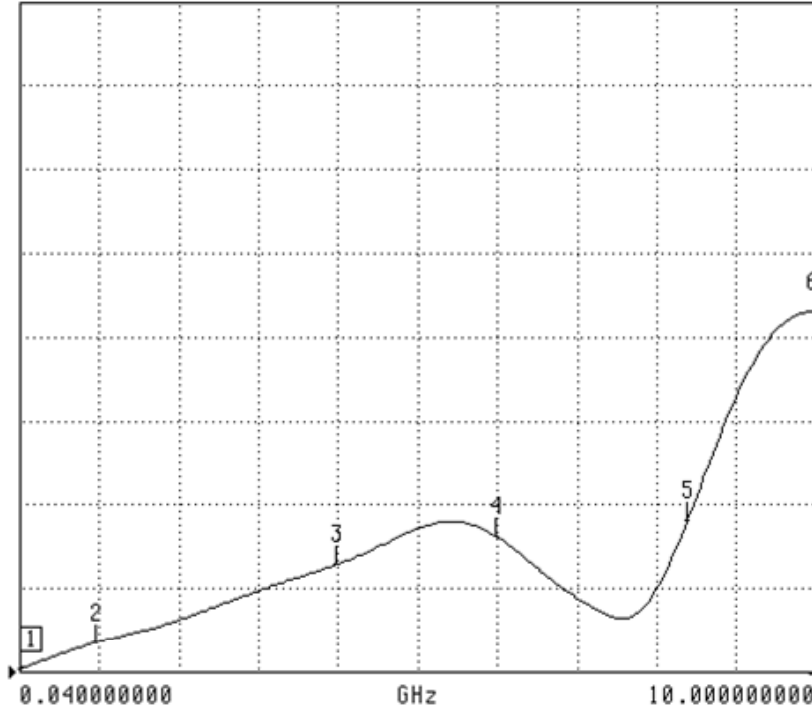
FGT

CH 3 - S11
0.0000 mm REF
0.000 dB OFFSET
0.00° OFFSET

SWR

REF=1.000 U

100.000 mU/DIV



MARKER 1
0.040000000 GHz
1.003 U

MARKER TO MAX
MARKER TO MIN

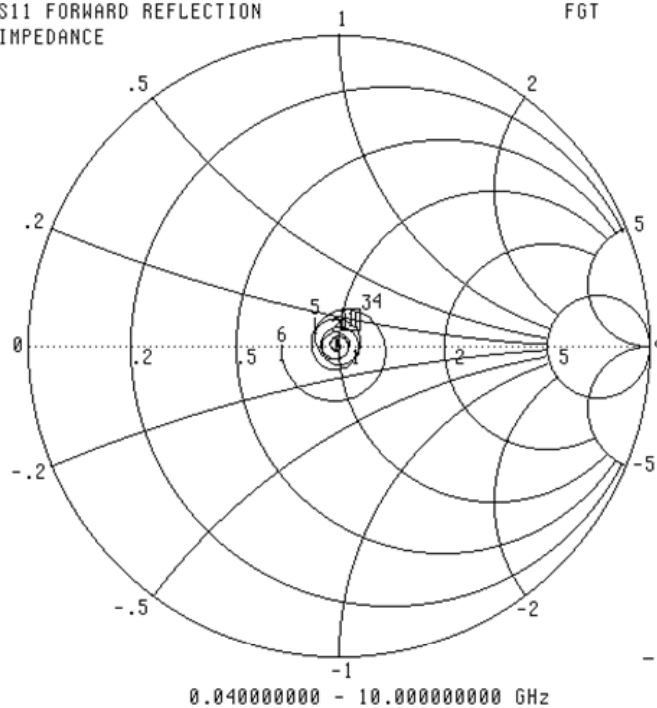
- | | | |
|---|------------------|---------|
| 2 | 1.000000000 GHz | 1.035 U |
| 3 | 4.000000000 GHz | 1.128 U |
| 4 | 6.000000000 GHz | 1.163 U |
| 5 | 8.400000000 GHz | 1.181 U |
| 6 | 10.000000000 GHz | 1.431 U |

MARKER READOUT FUNCTIONS

S11 FORWARD REFLECTION
IMPEDANCE

FGT

CH 4 - S11
0.0000 mm REF
0.000 dB OFFSET
0.00° OFFSET



MARKER 1
0.040000000 GHz
50.143 Ω
64.091 jΩ

MARKER TO MAX
MARKER TO MIN

- | | | | |
|---|------------------|----------|-----------|
| 2 | 1.000000000 GHz | 49.696 Ω | -1.702 jΩ |
| 3 | 4.000000000 GHz | 52.343 Ω | 5.755 jΩ |
| 4 | 6.000000000 GHz | 55.677 Ω | 6.249 jΩ |
| 5 | 8.400000000 GHz | 43.238 Ω | 3.469 jΩ |
| 6 | 10.000000000 GHz | 34.628 Ω | -3.337 jΩ |

MARKER READOUT FUNCTIONS

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RES-NET MICROWAVE